

MBRS120T3

Schottky Power Rectifier Surface Mount Power Package

Employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes, in surface mount applications where compact size and weight are critical to the system.

FEATURES:

- * Very Low Forward Voltage Drop (0.55 Volts Max @ 1.0A, T₁ = 25 °C)
- * Small Compact Surface Mountable Package
- * Highly Stable Oxide Passivated Junction
- * Guardring for Stress Protection
- * Pb / RoHS Free

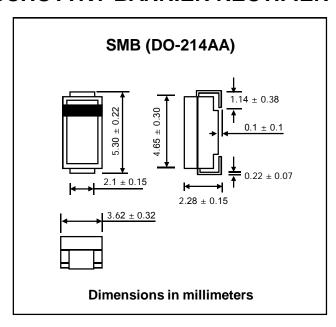
MECHANICAL DATA:

* Case: SMB Molded plastic

* Epoxy: UL94V-O rate flame retardant
* Lead: Lead Formed for Surface Mount
* Polarity: Color band denotes cathode end

* Mounting position : Any* Weight : 0.1079 gram

SCHOTTKY BARRIER RECTIFIER



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

RATING	SYME	OL VALUE	UNIT
Maximum Repetitive Reverse Voltage	V_{RR}	м 20	V
Maximum Working Peak Reverse Voltage	V_{RW}	м 20	V
Maximum DC Blocking Voltage	V _{DC}	20	V
Maximum Average Forward Rectified Current (T _L = 115 °C) I _{F(A\}	1.0	A
Maximum Non-repetitive Peak Surge Current	1	40	А
(Surge applied at rated load conditions half wave, single ph	ase)	40	
Maximum Instantaneous Forward Voltage (Note 1)	V _E	0.60	V
$(I_F = 1.0 \text{ A}, T_J = 25 ^{\circ}\text{C})$	V _F	0.00	V
Maximum Instantaneous Reverse Current (Note1) at T _J	= 25 °C	1.0	mA
at T _J	= 100 °C	10	
Thermal Resistance - Junction to Lead (T _L = 25 °C)	R _{eJ}	L 12	°C/W
Operating Junction Temperature	T _J	- 65 to +125	°C

Note: (1) Pulse Test: Pulse Width = 300µs Duty Cycle ≤ 2%.

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RATING AND CHARACTERISTIC CURVES (MBRS120T3) FIG.1 - CURRENT DERATING FIG.2 - TYPICAL POWER DISSIPATION 1.0 SQUARE WAVE AVERAGE FORWARD CURRENT, (A) AVERAGE POWER DISSIPATION (WATTS) DC T_J = 125°C 0.8 0.6 3 2 0.2 0 0 80 100 105 110 115 95 AVERAGE FORWARD CURRENT, (A) LEAD TEMPERATURE, (°C) FIG.3 - TYPICAL FORWARD VOLTAGE FIG.4 - TYPICAL REVERSE LEAKAGE CURRENT REVERSE LEAKAGE CURRENT, INSTANTANEOUS FORWARD CURRENT, (A) T_C = 100 °C (mA) T_C = 25 °C 0.1 0.01 0.01 0.2 0.3 0.4 0.5 0.6 0.7 0.8 0.9 INSTANTANEOUS FORWARD VOLTAGE, (V) REVERSE VOLTAGE, (V) FIG. 5 TYPICAL CAPACITANCE 200 Note :TYPICAL CAPACITANCE AT 0 V = 160 pF 180 160 CAPACITANCE, (pF) 140 120 100 80 60 40 20 REVERSE VOLTAGE, (V)

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